



IGBT Modules

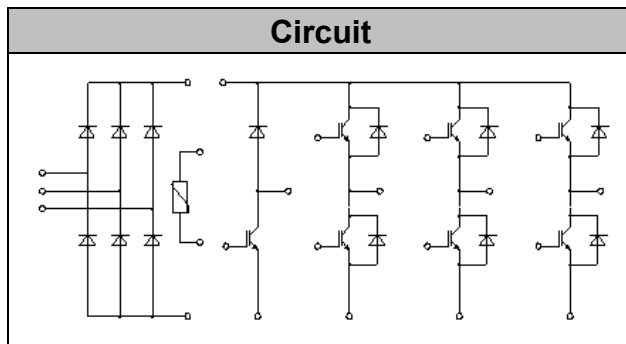
V_{CES}	1200V
I_C	25A

Applications

- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)

Features

- Low switching losses
- Low $V_{ce(sat)}$ with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Isolated heatsink using DBC technology
- Maximum junction temperature 175°C



IGBT- inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_c=100^{\circ}C, T_{vjmax}=175^{\circ}C$	25	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	50	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_c=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	175	W



IGBT- inverter Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$, $I_C=1.2mA$, $T_{vj}=25^{\circ}C$	5.2	5.8	6.4	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V$, $V_{GE}=0V$, $T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=25A$, $V_{GE}=15V$, $T_{vj}=25^{\circ}C$		1.85	2.25	V
		$I_C=25A$, $V_{GE}=15V$, $T_{vj}=125^{\circ}C$		2.15		
		$I_C=25A$, $V_{GE}=15V$, $T_{vj}=150^{\circ}C$		2.25		
Gate Charge	Q_G			0.20		uC
Input Capacitance	C_{ies}	$V_{CE}=25V$, $V_{GE}=0V$, $f=1MHz$, $T_{vj}=25^{\circ}C$		1.90		nF
Reverse Transfer Capacitance	C_{res}			0.10		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V$, $V_{GE}=20V$, $T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=25A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=20\Omega$ $T_{vj}=25^{\circ}C$		26		ns
Rise Time	t_r			17		ns
Turn-off Delay Time	$t_{d(off)}$			194		ns
Fall Time	t_f			181		ns
Energy Dissipation During Turn-on Time	E_{on}			1.62		mJ
Energy Dissipation During Turn-off Time	E_{off}			1.44		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=25A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=20\Omega$ $T_{vj}=125^{\circ}C$		28		ns
Rise Time	t_r			21		ns
Turn-off Delay Time	$t_{d(off)}$			284		ns
Fall Time	t_f			212		ns
Energy Dissipation During Turn-on Time	E_{on}			2.4		mJ
Energy Dissipation During Turn-off Time	E_{off}			2.18		mJ
SC Data	I_{sc}	$T_p \leq 10\mu s$, $V_{GE}=15V$, $T_{vj}=150^{\circ}C$, $V_{cc}=900V$, $V_{CEM} \leq 1200V$		120		A



Diode-inverter Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		25	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	50	A
I^2t -value	I^2t	$V_R=0, t_p=10\text{ms}, T_{vj}=125^{\circ}\text{C}$	90.0	A^2s
		$V_R=0, t_p=10\text{ms}, T_{vj}=150^{\circ}\text{C}$	75.0	

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=25\text{A}, T_{vj}=25^{\circ}\text{C}$		2.10	2.50	V
		$I_F=25\text{A}, T_{vj}=125^{\circ}\text{C}$		2.20		
		$I_F=25\text{A}, T_{vj}=150^{\circ}\text{C}$		2.20		
Recovered Charge	Q_{rr}	$I_F=25\text{A}$		2.52		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt=1700\text{A}/\mu\text{s}$		48.5		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^{\circ}\text{C}$		0.94		mJ
Recovered Charge	Q_{rr}	$I_F=25\text{A}$		50.8		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt=1700\text{A}/\mu\text{s}$		50.0		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=125^{\circ}\text{C}$		1.75		mJ



IGBT-brake-chopper Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_c=100^{\circ}C, T_{vjmax}=175^{\circ}C$	25	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	50	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_c=25^{\circ}C, T_{vjmax}=175^{\circ}C$	175	W

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.2mA, T_{vj}=25^{\circ}C$	5.2	5.8	6.4	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=25A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.85	2.25	V
		$I_C=25A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.15		
		$I_C=25A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.25		
Gate Charge	Q_G			0.20		μC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		1.90		nF
Reverse Transfer Capacitance	C_{res}			0.10		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=25A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=20\Omega$ $T_{vj}=25^{\circ}C$		26		ns
Rise Time	t_r			17		ns
Turn-off Delay Time	$t_{d(off)}$			194		ns
Fall Time	t_f			181		ns
Energy Dissipation During Turn-on Time	E_{on}			1.62		mJ
Energy Dissipation During Turn-off Time	E_{off}			1.44		mJ



Turn-on Delay Time	$t_{d(on)}$	$I_C = 25\text{ A}$ $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 20\Omega$ $T_{vj} = 125^\circ\text{C}$		28		ns
Rise Time	t_r			21		ns
Turn-off Delay Time	$t_{d(off)}$			284		ns
Fall Time	t_f			212		ns
Energy Dissipation During Turn-on Time	E_{on}			2.4		mJ
Energy Dissipation During Turn-off Time	E_{off}			2.18		mJ
SC Data	I_{sc}	$T_p \leq 10\mu\text{s}, V_{GE} = 15\text{ V}, T_{vj} = 150^\circ\text{C},$ $V_{cc} = 900\text{ V}, V_{CEM} \leq 1200\text{ V}$		120		A

Diode-Brake-Chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC Forward Current	I_F		15	A
Repetitive Peak Forward Current	I_{FRM}	$t_p = 1\text{ ms}$	30	A
I^2t -value	I^2t	$V_R = 0, t_p = 10\text{ ms}, T_{vj} = 125^\circ\text{C}$	16.0	A^2s
		$V_R = 0, t_p = 10\text{ ms}, T_{vj} = 150^\circ\text{C}$	14.0	

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F = 15\text{ A}, T_{vj} = 25^\circ\text{C}$		2.00	2.65	V
		$I_F = 15\text{ A}, T_{vj} = 125^\circ\text{C}$		2.10		
		$I_F = 15\text{ A}, T_{vj} = 150^\circ\text{C}$		2.10		
Recovered Charge	Q_{rr}	$I_F = 15\text{ A}$		1.20		μC
Peak Reverse Recovery Current	I_{rr}	$V_R = 600\text{ V}$ $-di_F/dt = 600\text{ A}/\mu\text{s}$		13.0		A
Reverse Recovery Energy	E_{rec}	$T_{vj} = 25^\circ\text{C}$		0.37		mJ
Recovered Charge	Q_{rr}	$I_F = 15\text{ A}$		2.05		μC
Peak Reverse Recovery Current	I_{rr}	$V_R = 600\text{ V}$ $-di_F/dt = 600\text{ A}/\mu\text{s}$		12.0		A
Reverse Recovery Energy	E_{rec}	$T_{vj} = 125^\circ\text{C}$		0.68		mJ



Diode-Rectifier

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_j=25^{\circ}\text{C}$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_c=100^{\circ}\text{C}$	35	A
Maximum RMS Current at Rectifier Output	I_{RMSM}	$T_c=100^{\circ}\text{C}$	60	A
Surge Forward Current	I_{FSM}	$V_R=0, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	320	A
I^2t -value	I^2t	$V_R=0, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	510	A^2s

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F=10\text{A}, T_j=150^{\circ}\text{C}$		1.02		V
Reverse Current	I_R	$T_j=150^{\circ}\text{C}, V_R=1600\text{V}$			2	mA

NTC-Thermistor

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_c=100, R_{100}=493.3\Omega$	-5		5	%
Power Dissipation	P_{25}				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

**Module Characteristics** (T_C=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V _{isol}	t=1min, f=50Hz	2500			V
Maximum Junction Temperature	T _{jmax}				175	°C
Operating Junction Temperature	T _{vj op}		-40		150	°C
Storage Temperature	T _{stg}		-40		125	°C
Stray-inductance-module	L _{SCE}			30		nH
Module lead resistance, terminals-chip	R _{cc'+EE'}	T _C =25°C, per switch		5.00		mΩ
	R _{AA'+CC'}			6.00		
Thermal Resistance Junction-to Case	R _{θJC}	per IGBT-inverter		0.75	0.85	K/W
		per Diode-inverter		1.10	1.20	
		per IGBT-brake-copper		0.75	0.85	
		per Diode-chopper		1.30	1.45	
		per Diode-rectifier		0.90	1.25	
Thermal Resistance Case-to Sink	R _{θCS}	per IGBT-inverter		0.70		K/W
		per Diode-inverter		0.90		
		per IGBT-brake-copper		0.70		
		per Diode-chopper		1.05		
		per Diode-rectifier		0.95		
		per Module		0.037		
Mounting Force Per Clamp	F		30		80	N
Weight of Module	G			45		g

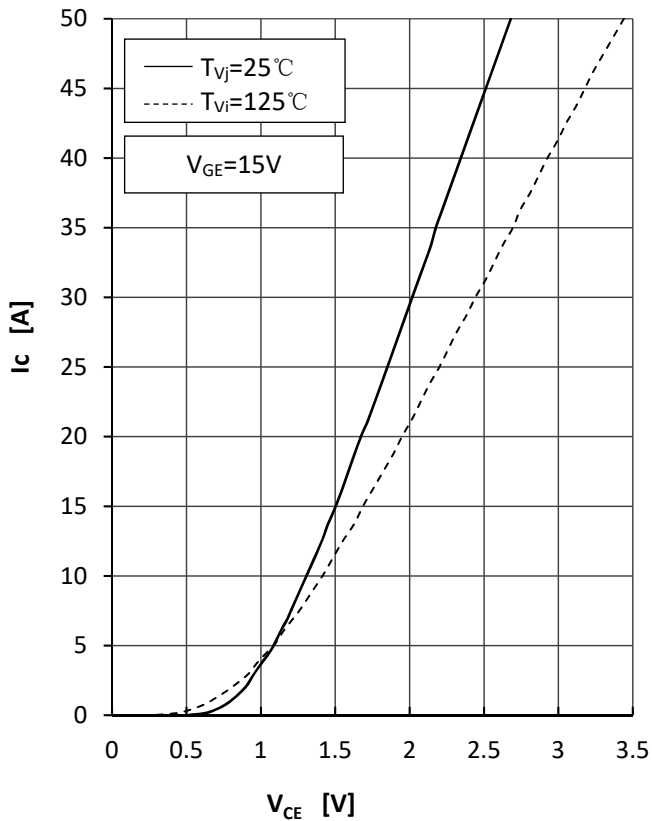


Fig1.IGBT Output Characteristics

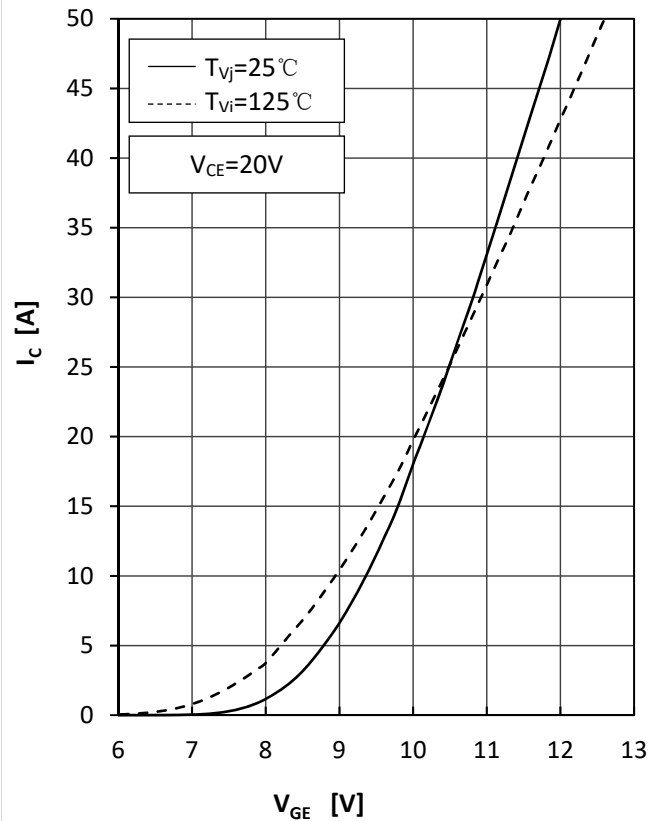


Fig2.IGBT Transfer Characteristics

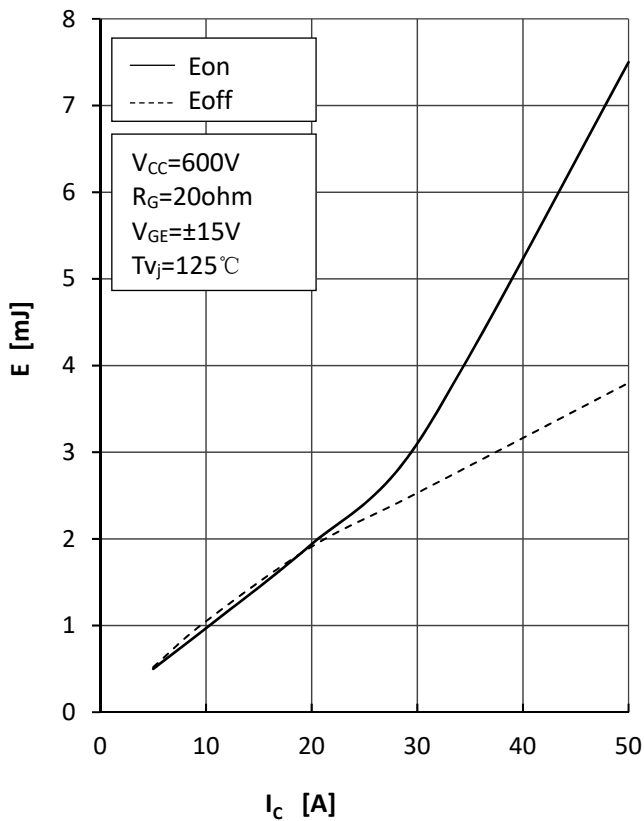


Fig3.IGBT Switching Loss vs.Ic

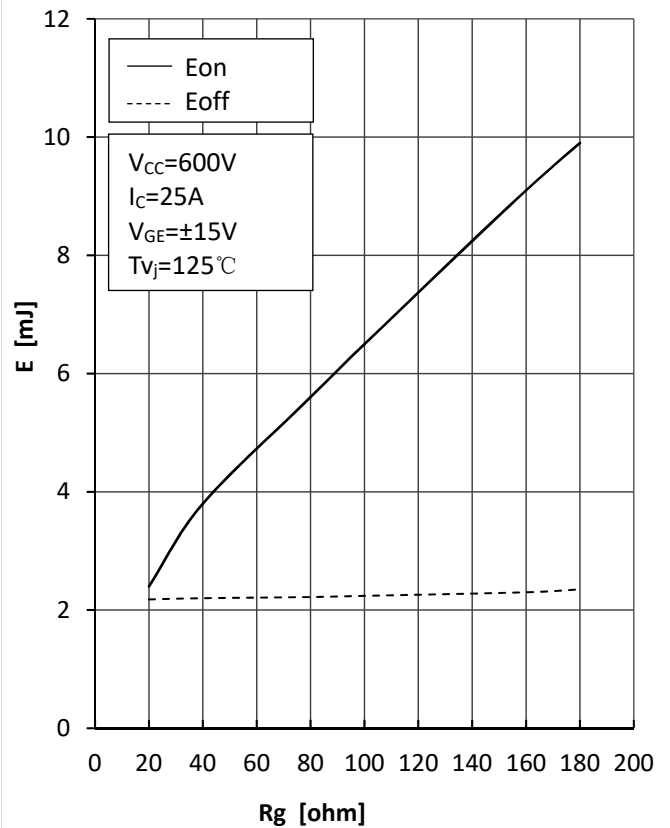
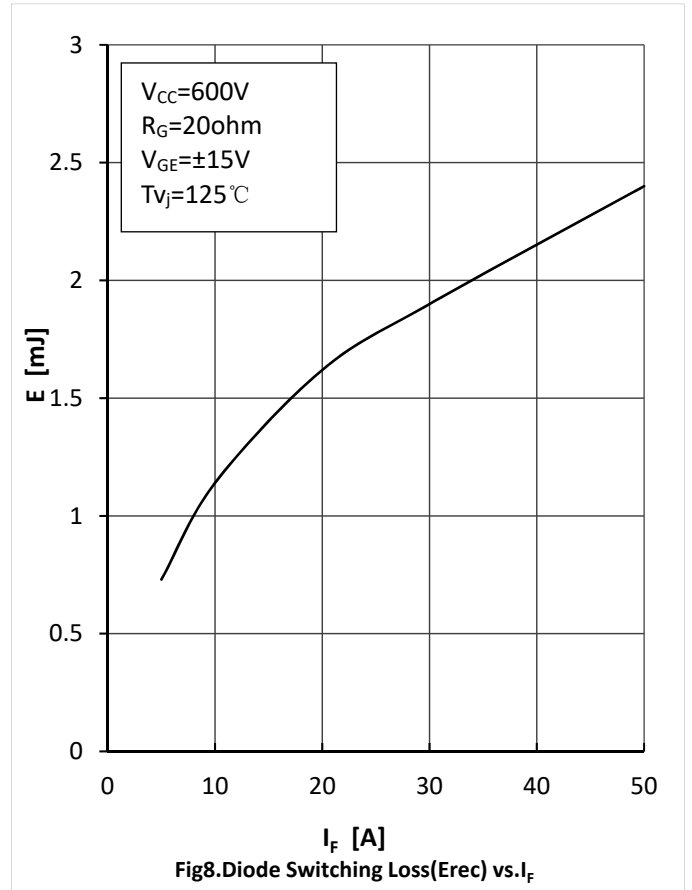
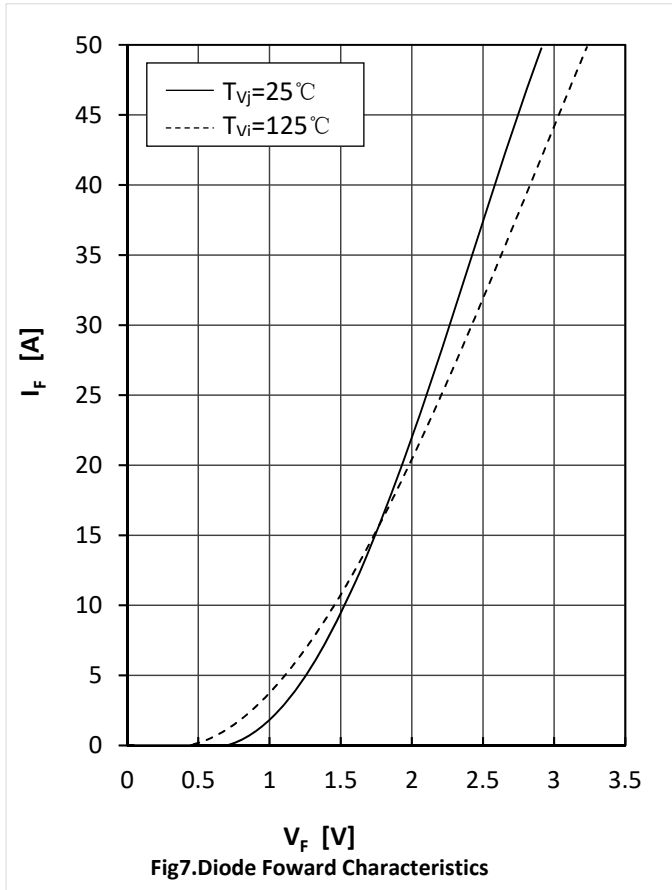
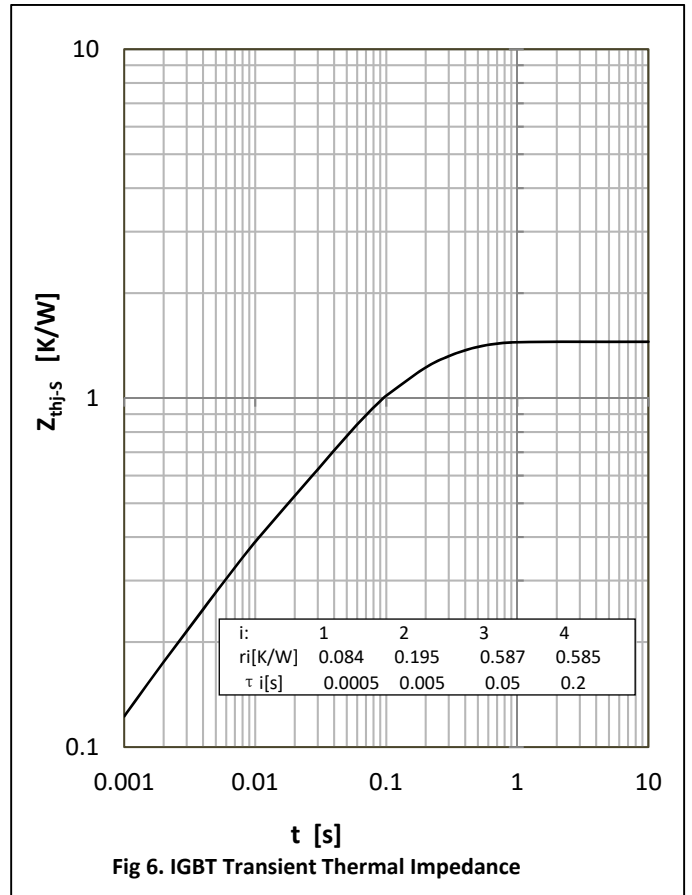
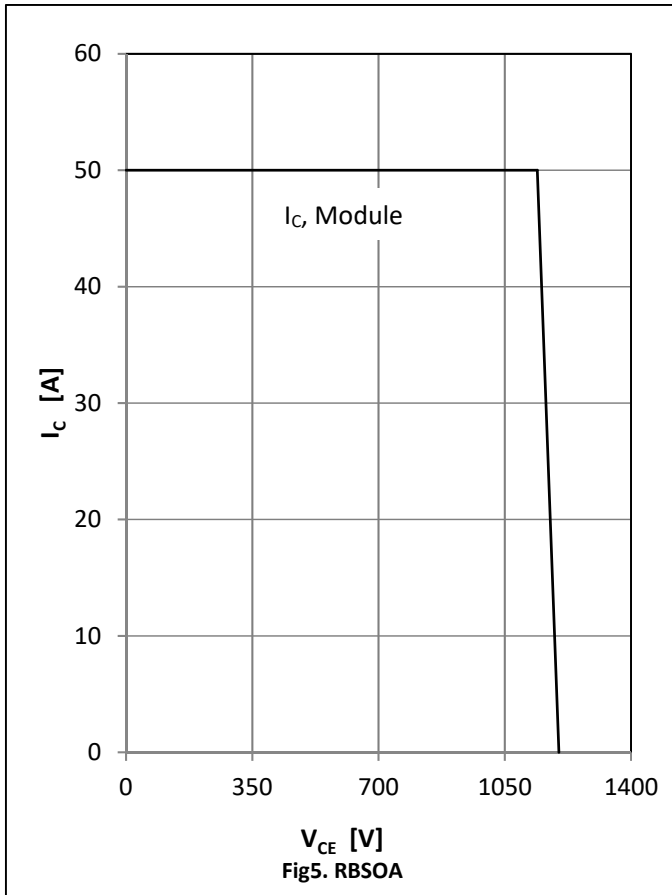


Fig4.IGBT Switching Loss vs.Rg



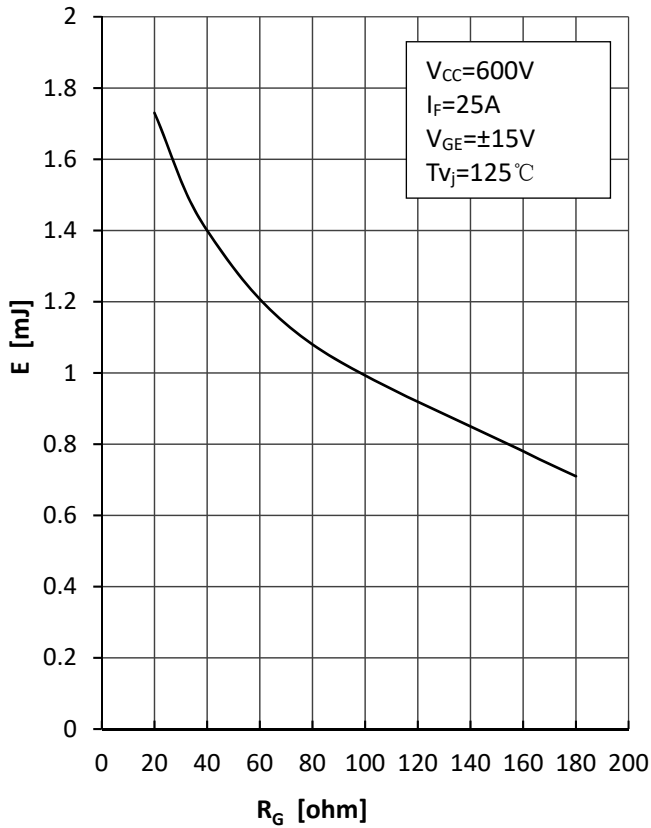


Fig9. Diode Switching Loss(E_{rec}) vs. R_g

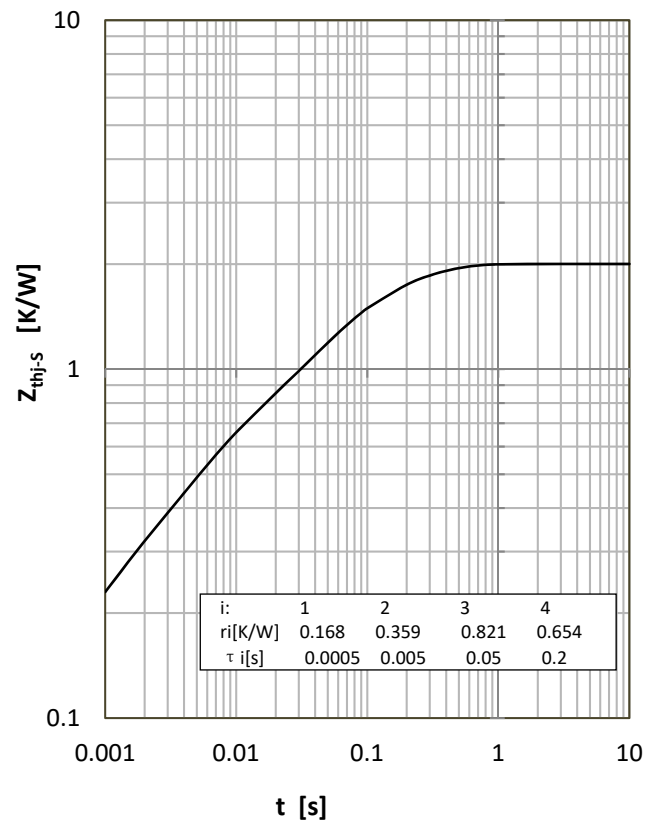


Fig10. Diode Transient Thermal Impedance

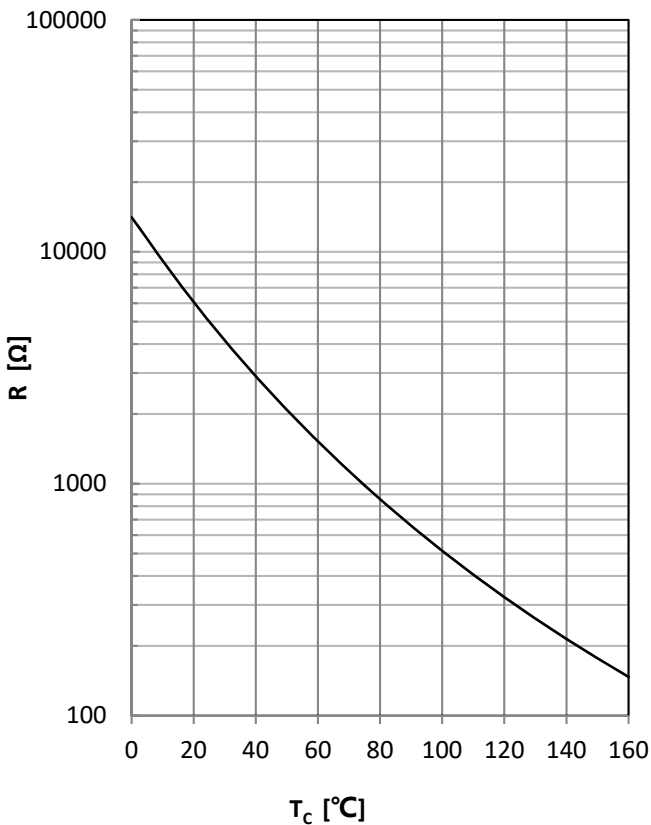


Fig 11. NTC Temperature Characteristic

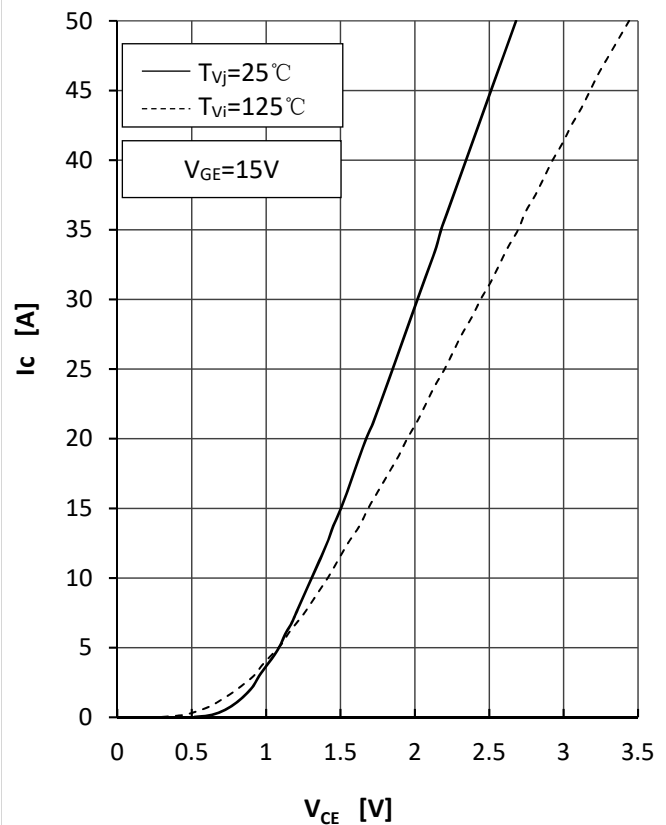
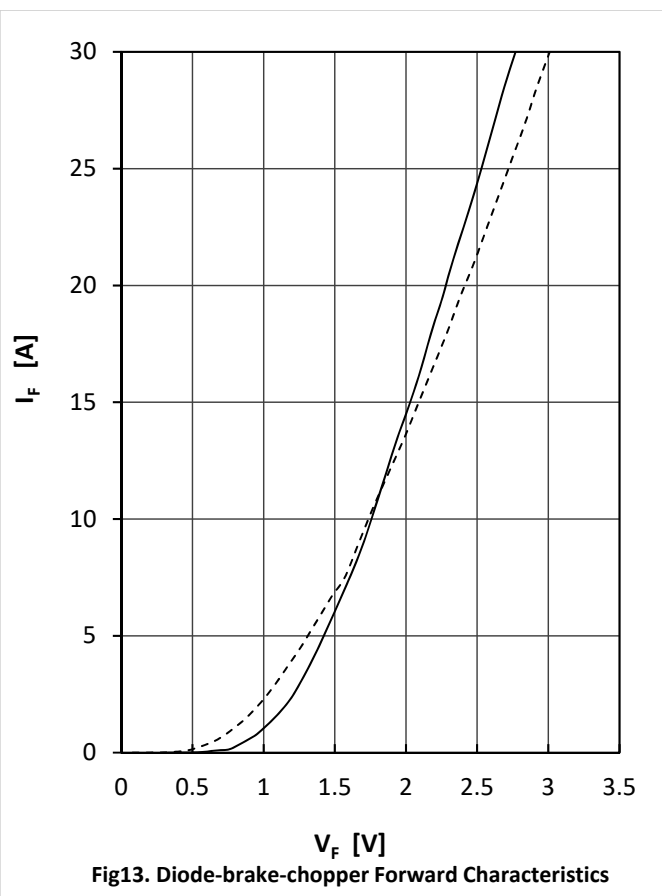
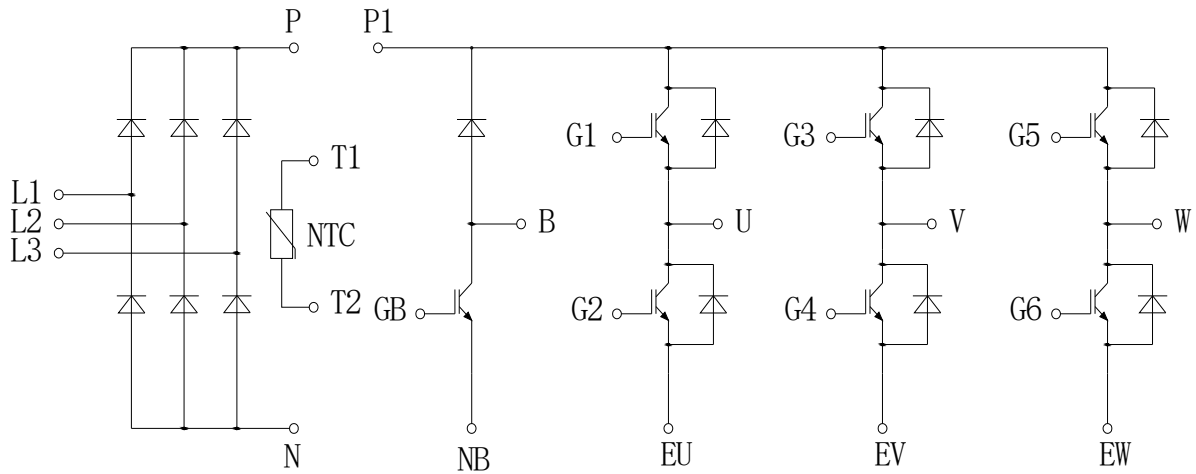


Fig12. IGBT-brake-Chopper output Characteristics

— $T_{vj}=25^{\circ}\text{C}$
- - - $T_{vj}=125^{\circ}\text{C}$



Circuit Diagram



Package Dimensions

